

Schottky barrier diode

RB471E

●Applications

Low current rectification
For switching power supplies

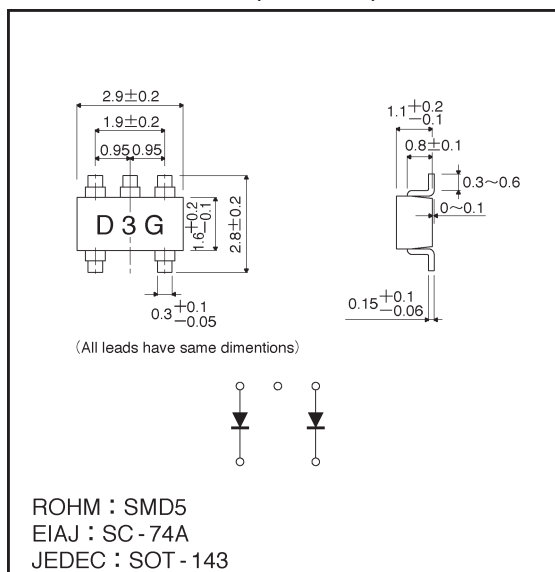
●Features

- 1) Small surface mounting type. (SMD5)
- 2) Two diodes in parallel.
- 3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.28	0.34	V	$I_F=10\text{mA}$
	V_{F2}	—	0.45	0.55	V	$I_F=100\text{mA}$
Reverse current	I_R	—	1	30	μA	$V_R=10\text{V}$
Capacitance between terminals	C_T	—	6.0	—	pF	$V_R=10\text{V}$, $f=1\text{MHz}$

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

